

TCAD simulations of LGAD devices [Wednesday!]

Wednesday, December 2, 2015 3:50 PM (20 minutes)

I will present preliminary results from simulated LGAD devices, before and after irradiation. Electrical properties and response to MIPs and alpha particles will be discussed, as a function of irradiation fluences, polarization voltage and device temperature.

Summary

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Session Classification: CMOS sensors and Sensor Producers